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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/783,495	95 02/20/2004		Yung-Cheng Chen	N1085-00251 [TSMC2003-083		
54657	7590	12/04/2006		EXAM	INER	
DUANE M	ORRIS I	LLP	NORTON, J	NORTON, JENNIFER L		
IP DEPART 30 SOUTH	,	•		ART UNIT	PAPER NUMBER	
		A 19103-4196	2121			
				DATE MAILED: 12/04/200	6	

Please find below and/or attached an Office communication concerning this application or proceeding.

Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)
10/783,495	CHEN ET AL.
Examiner	Art Unit
Jennifer L. Norton	2121

	Jennifer L. Norton	2121	
The MAILING DATE of this communication appear	ars on the cover sheet with t	he correspondence ado	ress
THE REPLY FILED 14 November 2006 FAILS TO PLACE THIS	APPLICATION IN CONDITIO	N FOR ALLOWANCE.	
1. The reply was filed after a final rejection, but prior to or on- this application, applicant must timely file one of the follow places the application in condition for allowance; (2) a Not a Request for Continued Examination (RCE) in complianc time periods:	the same day as filing a Notic ing replies: (1) an amendmen ice of Appeal (with appeal fee	e of Appeal. To avoid aba t, affidavit, or other evider) in compliance with 37 C	nce, which FR 41.31; or (3)
 a)	dvisory Action, or (2) the date set		
Examiner Note: If box 1 is checked, check either box (a) or (TWO MONTHS OF THE FINAL REJECTION. See MPEP 70 Extensions of time may be obtained under 37 CFR 1.136(a). The date of	6.07(f).		
have been filed is the date for purposes of determining the period of ext under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the s set forth in (b) above, if checked. Any reply received by the Office later may reduce any earned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL	ension and the corresponding am hortened statutory period for reply	ount of the fee. The appropr originally set in the final Off	iate extension fee ice action; or (2) as
 The Notice of Appeal was filed on A brief in compl filing the Notice of Appeal (37 CFR 41.37(a)), or any exter a Notice of Appeal has been filed, any reply must be filed AMENDMENTS 	sion thereof (37 CFR 41.37(e)), to avoid dismissal of the	ns of the date of ne appeal. Since
3. X The proposed amendment(s) filed after a final rejection, b			ecause
 (a) They raise new issues that would require further cor (b) They raise the issue of new matter (see NOTE below 		NOTE below);	
(c) ☐ They raise the issue of new matter (see NOTE below (c) ☐ They are not deemed to place the application in bett appeal; and/or		ly reducing or simplifying	the issues for
(d) They present additional claims without canceling a c	_	y rejected claims.	
NOTE: See Continuation Sheet. (See 37 CFR 1.11		- 0	(DTOL 224)
 The amendments are not in compliance with 37 CFR 1.12 Applicant's reply has overcome the following rejection(s): 		n-Compilant Amendment	(PTOL-324).
6. Newly proposed or amended claim(s) would be all		rate timely filed amendme	ant canceling the
non-allowable claim(s).	·	•	_
7. For purposes of appeal, the proposed amendment(s): a) the how the new or amended claims would be rejected is proved the status of the claim(s) is (or will be) as follows:] will be entered and an e	explanation of
Claim(s) allowed:			
Claim(s) objected to: Claim(s) rejected: 1-22.	•		
Claim(s) withdrawn from consideration:		•	
AFFIDAVIT OR OTHER EVIDENCE		•	
 The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e). 	before or on the date of filing I sufficient reasons why the at	a Notice of Appeal will <u>no</u> fidavit or other evidence i	ot be entered s necessary and
9. The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to o showing a good and sufficient reasons why it is necessary	vercome <u>all</u> rejections under a	ippeal and/or appellant fa	ils to provide a
10. The affidavit or other evidence is entered. An explanation	•		•
REQUEST FOR RECONSIDERATION/OTHER 11. The request for reconsideration has been considered but	does NOT place the applicat	ion in condition for allowa	nce hecause:
See Continuation Sheet.		Ion in condition for allowa	nice because.
12. Note the attached Information Disclosure Statement(s). (PTO/SB/08) Paper No(s)	- , - fr	
13. Other:	fint !	The state of the s	
	Arthony	/Knight	
	Supervisory Pa	Itent Examiner	

Group 3600

Continuation of 3. NOTE: Applicant's arguments, see Remarks pgs. 6-8, filed 14 November 2006 with respect to the rejection of claims 1-4 and 9-11 under 35 U.S.C. 102 (b) have been fully considered but they are not persuasive.

The Examiner respectfully transverse the Applicant's argument U.S. Patent No. 5,409,538 (hereinafter Nakayama) does not disclose, "controlling the exposure energy with a feedback process control signal of critical dimensions, and further controlling the exposure energy with a feed forward process control signal of a compensation amount that compensates for wafer variations.", and "controlling an exposure energy with a feedback process control signal of critical dimension (CD) and controlling the exposure energy with a feed forward process control signal of a compensation amount that compensates for wafer thickness variations such as used to control exposure energy when patterning a substrate."

Nakayama discloses, (col. 6, lines 48-55) "Accordingly, a feedback control of the process conditions of the forming and treating apparatus such as to make constant the film thickness determined in the above-mentioned manner ensures stabilization of the forming and treating apparatus, even if the reflectivity of the wafer before the formation and treatment of the thin film is varied due to variations in the process conditions."

(col. 1, lines 60-67 and col. 2, lines 1-4) "In thin film forming and treating steps such as the film forming step and etching step before or after the exposure step, as shown in FIG. 4, due to the increase in the diameter of the wafer formed and treated and the decrease in the thickness of film, the thickness and optical properties of the thin film formed and treated are varied with slight variations in the production process conditions. In a thin film forming and treating apparatus, therefore, it is necessary to constantly monitor the thickness and optical properties of the thin film being formed or treated, and to control the process conditions so as to keep constant the thickness and optical properties of the thin film."

(col. 15, lines 43-53) "When the exposure, coating and baking conditions are controlled once for a few wafers, an effect on automation of the conventional preliminary operation is obtained. Where process conditions in the same manufacturing apparatus vary on a wafer basis, it is possible to control the exposure, coating and baking conditions on wafer basis. Furthermore, where variations in the process conditions within a wafer are important, it is possible to control the exposure condition on a chip basis and to control the coating and baking conditions within the wafer."

As previously stated in the Final Office Action mailed on 23 August 2006, Nakayama discloses, (col. 15, lines 12-21) "The data sent from the optical property measuring system 108 is used to correct the data sent from the optical property measuring system 56. Based on the results of correction, the process controlling system 45 calculates the optimum exposure energy as a process variable for the exposure step and also calculate variations in process conditions for the photoresist coating step." (col. 15, lines 27-41) "Then, exposure is carried out for the optimum exposure time, whereby stabilization of pattern size is contrived. The variations in process conditions for the photoresist coating step obtained by the process controlling system 45 are fed back through an interface 102 to the photoresist coating machine 49, in order to stabilize the photoresist coating and baking conditions.

In this embodiment, the optical property measuring system 108 and the optical property measuring system 56 can be connected to a plurality of photoresist coating machines to stabilize the photoresist coating and baking conditions constituting the production process conditions, and to a plurality of projection aligners fed with wafers for which the optimum exposure energy has been determined."

Hence, Nakayama discloses the feed forward process control, by using "the results of correction" (i.e. a compensation value determined based on the measured value outputted from the system) to calculate the optimum energy in process controlling system 45 to drive the system to a desired response.

The Applicant has raised the limitations, "used to control exposure energy when patterning a substrate" and "a signal of critical dimension, such as a width or length of a pattern ... is generated based on data collected from a patterned photoresist layer" is not recited in the rejected claims, hence these limitations have not been given any patentable weight. Futhermore, the limitations are recited in the Remarks are not believed to patentable even if the claims were to be appropriately amended to include the limitation.

The Examiner respectfully transverse the Applicant's argument Nakayama does not disclose, "feedback process control signal of critical dimension".

Nakayama discloses, (col. 6, lines 48-55) "On the other hand, where the thin film to be formed and treated is one which is formed and treated by a film forming apparatus, an etching apparatus or a thin film forming apparatus other than the photoresist coating machine, the complex index of refraction N (=n-i.multidot..kappa.) of the thin film is varied during the formation or treatment. Therefore, it is possible to determine the variation with time of the thickness d of the thin film being formed and treated from equation (1) by preliminarily measuring n' I.sub.2 and N, measuring the reflectivity R' of the wafer before the formation and treatment of the thin film, and correcting the measurements of variation of the reflectivity R with time during the formation and treatment of the thin film. Accordingly, a feedback control of the process conditions of the forming and treating apparatus such as to make constant the film thickness determined in the above-mentioned manner ensures stabilization of the forming and treating apparatus, even if the reflectivity of the wafer before the formation and treatment of the thin film is varied due to variations in the process conditions."

Futhermore, by the Applicant's admission that ""critical dimensions", CDs, refers to "dimensions of the smallest geometrical features (width of interconnect line, contracts, trenches, etc) (see Remarks, pg. 7, par. 14-16)"" has supported the Examiner's ascertainthat Nakayama does included measuring and controlling a critical dimension, since a trench is a geometrical feature etched into semiconductor substrate; anisotropic etch in the direction normal to the surface (i.e. depth/thickness) as defined in http://www.semiconductorglossary.com/default.asp?searchterm=trench.

In addition, Applicant's arguments, see Remarks pgs. 8-9, filed 14 November 2006 with respect to the rejection of claims 5-8 and 12-22 under 35 U.S.C. 103 (a) have been fully considered but they are not persuasive; and stand rejected as set forth in Final Office action mailed on 23 August 2006.

Continuation of 11. does NOT place the application in condition for allowance because: The Applicant has not overcome the prior art in the rejections of claims 1-22 as set forth in the Final Office Action mailed on 23 August 2006. Hence, the Applicant's claimed invention is not considered patentably distinct over the prior art.